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Leubner, P.; Lunczer, L.; Brüne, C.; Buhmann, H.; Molenkamp, L.W.

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Strain Engineering of the Band Gap of HgTe Quantum Wells Using Superlattice Virtual Substrates

Philipp Leubner,* Lukas Lunczer, Christoph Brüne, Hartmut Buhmann, and Laurens W. Molenkamp

* Experimentelle Physik III, Physikalisches Institut, Universität Würzburg, Am Hubland, D-97074 Würzburg, Germany

The HgTe quantum well (QW) is a well-characterized two-dimensional topological insulator (2D TI). Its band gap is relatively small (typically on the order of 10 meV), which restricts the observation of purely topological conductance to low temperatures. Here, we utilize the strain dependence of the band structure of HgTe QWs to address this limitation. We use CdTe-Cd_{0.5}Zn_{0.5}Te strained-layer superlattices on GaAs as virtual substrates with adjustable lattice constant to control the strain of the QW. We present magneto-transport measurements, which demonstrate a transition from a semimetallic to a 2D-TI regime in wide QWs, when the strain is changed from tensile to compressive. Most notably, we demonstrate a much enhanced energy gap of 55 meV in heavily compressively strained QWs. This value exceeds the highest possible gap on common II-VI substrates by a factor of 2–3, and extends the regime where the topological conductance prevails to much higher temperatures.

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one readily derives the limiting nature of the atomic-layer epitaxy process \cite{11,12}, a single superlattice period and taking into account the self-SLS satellites. By the balancing of the forces acting within 1 monolayer CdTe-layer growth time $t_{\text{CT}}$ and Te beam equivalent pressure $q_{\text{Te}}$, which are both straightforwardly accessible in the experiment. In Eq. (1), $f$ is the lattice

$$a_{\text{SLS}} = a_{\text{CT}} \left[ 1 + \frac{f}{1 + a(t_{\text{CT}} \times q_{\text{Te}})} \right], \quad (1)$$

mismatch between unstrained CdTe and Cd$_{0.2}Zn_{0.8}$Te and $a_{\text{CT}}$ is the lattice constant of CdTe \cite{13}. The parameter $\alpha$ contains material (stiffnesses $\epsilon_{ij}$ \cite{14} and Cd$_{0.2}Zn_{0.8}$Te epilayer thickness) and process-specific parameters (normalized CdTe growth speed). The effective lattice constant $a_{\text{SLS}}$ is deduced from the angular spacing of the GaAs substrate ("S") and the zero-order Bragg reflection of the SLS ("C"). Figure 1(c) shows the obtained $a_{\text{SLS}}$ for a set of SLS as a function of $t_{\text{CT}} \times q_{\text{Te}}$. A fit of Eq. (1), with $\alpha = 3.4 \times 10^5$ s$^{-1}$ Torr$^{-1}$ (black line), is in good agreement with the data. Thus, $a_{\text{SLS}}$ can be controlled over a wide range by simply adjusting $t_{\text{CT}} \times q_{\text{Te}}$. This degree of freedom allows for precise control of the strain in HgTe (001) epilayers and, in turn, offers new ways to modify the band structure of bulk layers and QWs. To demonstrate the scope of the modifications of the band structure, we have fabricated a set of three QWs, A, B, and C, with distinct strain and thickness parameters for magnetotransport measurements. Samples A and B are thick QWs with almost identical thickness ($d_{\text{QW}} = 16$ and 15 nm), and similar top and bottom barrier layers (Cd$_{0.2}Hg_{0.8}$Te with $d_{\text{bar}} = 17$ nm, each). The virtual substrates, however, are different. Sample A is grown on a thick, relaxed CdTe (001) epilayer grown on GaAs, which gives rise to tensile strain. Samples B and C are grown on two different SLS that induce moderate and large compressive strain on the respective QWs. In sample C, a solid solution of (Zn,Cd,Hg)Te is used as barrier material ($d_{\text{bar}} = 18$ nm) (instead of the standard Cd$_{0.2}Hg_{0.8}$Te), to lower the mismatch between substrate and barriers, thus avoiding relaxation of the heterostructure. The QW thickness of sample C is $d_{\text{QW}} = 7.5$ nm. HRXRD 20 - $\omega$ scans of the (004) diffraction profiles of all three samples are shown in Fig. 2(a). The color coding of data (red: sample A; blue: sample B; green: sample C) hold for the rest of this work. The strain in the HgTe layers, deduced from the S-0 angular separation, is $\epsilon = -0.3\%$ for sample A, $+0.4\%$ for sample B, and $+1.4\%$ for sample C. Unlabeled reflections are caused by the (Zn,Cd,Hg)Te barriers. The barriers and the QW of all samples are fully strained, as verified by comparing the diffraction profiles with appropriate simulations (black lines). It is worth noting that the symmetric measurement geometry probes the out-of-plane response of the lattice constants to the in-plane strain. The magnitude of the response is determined by the lattice constant mismatches of SLS to barrier and SLS to QW, respectively, and the Poisson’s ratios of the materials. Arrows highlight the strain-induced shift of the barrier reflection of samples A and B. Note that relaxation of the HgTe layer would be seen as a lowered shift of the top barrier reflection \cite{15}. From its angular position, the composition of the barriers of sample C can be estimated as Zn$_{0.20}$Cd$_{0.56}$Hg$_{0.24}$Te. Remarkably, due to the large mismatch between QW and barriers, the QW of sample C is directly visible in the diffraction pattern as an isolated set of fringes [labeled “Q” in Fig. 2(a),
Figure 2(a) shows the band structures of the three QWs, calculated using an eight-band $k \cdot p$ model [16]. The variety in energy dispersions accessible by varying the strain and the thickness of the QW is evident. Upon comparing samples A and B, one observes that the strain in the layers primarily affects the shape of the valence band (VB) and causes a transition from a semimetal-like system to a direct-band-gap semiconductor. From the band structure of samples A, B, and C (from top to bottom), one observes that the strain-induced shift of the Fermi level at the van Hove singularity ($\epsilon_v$) from negative to positive values shifts the Fermi energy from the VB into the CB. This is apparent by a transition from $p$-conducting to $n$-conducting behavior that is reflected in a sign change of the Hall resistance $R_{xy}$. As shown in Fig. 3(a), the presence or absence of a band overlap in samples A and B results in markedly different characteristics of $R_{xy}$ (traces with similar labels are chosen such that the carrier densities are equal within experimental resolution). When the Fermi level is deep in the CB, the Hall resistance in both samples is purely electron-like, and both traces are linear (traces labeled “$n$”). As the gate voltage is lowered, a pronounced curvature is observed in $R_{xy}$ for sample A (trace “c”). This is characteristic of a system with coexisting electron- and hololike carriers of different mobilities [17], and indicates an overlap of the CB and VB [18]. In the same gate voltage regime, sample B is highly resistive, and no Hall voltage measurement is possible, implying that the Fermi energy is in the band gap. Finally, for strong negative gate voltages, an entirely linear trace is recovered for sample B, while, in contrast, two-carrier conductance persists in sample A (traces “p”).

We interpret this as reflecting the effective pinning of the Fermi level at the van Hove singularity (“camel’s back”) in the VB density of states in sample A.

Our data allow for a more detailed analysis of the evolving electron and hole densities of sample A. As soon as the Fermi energy intersects with the VB, two-carrier...
conductance sets in, and nonconstant $dR_{xy}/dB$ is evidence that, at low fields, the Hall resistance is no longer described by the simple single-carrier expression $R_{xy} = B(ne)^{-1}$. Experimentally, we observe this effect for negative gate voltages larger than $U_G = -0.4$ V [Fig. 3(b)]. The onset of two-carrier conductance allows us to estimate the energy overlap $E_{ov}$ of the VB and CB. A simultaneous fit of $R_{xy}$ and $R_{ex}$ to the standard two-carrier Drude model [17] yields the density of electron- and holelike carriers $n_e$ and $n_h$. Fits are shown in Fig. 3(a) as dashed lines. The resulting densities for the whole measurement set are shown in Fig. 3(c), together with the net density $n$, extracted from $R_{xy}$ at higher fields. The $n$-type carrier density at the onset of two-carrier conductance (black arrow) is $n_e^* = 5.5 \times 10^{10}$ cm$^{-2}$. Using $E_{ov} = E_F = n_e^* \pi \hbar^2 m_e^{-1}$, we obtain $E_{ov} = 4.5$ meV for the band overlap, which is slightly larger than the value inferred from band structure calculations [$E_{ov} = 3.5$ meV; see Fig. 2(c), top]. The electron effective mass in the CB is taken as $m_e = 0.028 m_0$ ($m_0$ is the mass of a free electron), in agreement with the $k \cdot p$ model calculations.

Finally, we discuss thermal activation studies of conductance, which allows us to discriminate between metallic sheet conductance at the charge neutrality point (sample A) and edge state conductance (samples B and C), and to estimate the magnitude of the strain-induced band gap of samples B and C. To distinguish between current flowing in the bulk of the QW and one-dimensional edge current, two Hall bars with different dimensions have been fabricated for each QW [inset in Fig. 4(a)]. Whereas the width-to-length ratio is identical ($w/l = 1/3$) for both Hall bars, the length of the gated edge changes by roughly a factor of 10 ($l_{edge} = 58$ and 620 μm). For temperatures in the range from $T = 1.8$ to 90 K, minimum values of the longitudinal conductance $G_{min}$ are measured at gate voltages corresponding to the situation when the Fermi energy is located at the charge neutrality point for sample A and the mid-band-gap position for samples B and C. The results are plotted in Fig. 4(a). Sample A (red curves) shows a high $G_{min}$, which changes only moderately with temperature. The observed low-temperature increase of $G_{min}$ with temperature was reported previously in Ref. [19] and has been attributed to long-range disorder scattering [20]. We suggest that the decrease in $G_{min}$ at higher $T$ is due to enhanced phonon scattering. The fact that $G_{min}$ is qualitatively similar for the large and small Hall bar indicates that the current flows in the bulk of the QW (as mentioned above, $w/l$, relating two-dimensional conductance to conductivity, is the same in both devices). The behavior of samples B and C is significantly different. For all temperatures, $G_{min}$ is much smaller than in sample A, and a thermally activated increase in conductance is observed, as typical for semiconductors. A logarithmic plot of the high-temperature data ($T > 10$ K) of samples B and C versus $T^{-1}$ is shown in Fig. 4(b). As a clear indication of edge channel transport in the low-temperature regime, we observe that $G_{min}$ of both samples tends to saturate, and the saturation values of large and small Hall bar roughly scale with the inverse of the edge channel length (10/1). Since the edge length of both Hall bars significantly exceeds the inelastic mean-free path of the QSH edge channels [11], and thus the number of scattering events is approximately proportional to the length of the channel [21], this is an expected signature of edge channel transport. With increasing temperature, the thermally activated conductance over the whole area of the mesa becomes dominant. It is possible to extract the band gap from the conductance in the high-temperature regime. By fitting the measured $G_{min}$ of the large Hall bar to

\[
G_{min} = G_0 \exp \left(- \frac{E_G}{2 k_B T} \right),
\]

we obtain $E_G = 17$ and 55 meV for samples B and C [solid lines in Fig. 4(b)], in good agreement with band structure calculations [$E_G = 16$ and 55 meV; see Fig. 2(b), center and bottom]. Reliable fits of Eq. (2) are only possible for the large Hall bars, since the QSH edge state conductance of the small Hall bars substantially contributes to the total conductance even at high temperatures.

In conclusion, we have presented a method to significantly increase the band gap of HgTe based 2D TIs, based on strain engineering via dedicated CdTe-Cd$_{0.5}$Zn$_{0.5}$Te...
SLS virtual substrates. In particular, we have shown that applying compressive strain to QWs results in energy gaps as high as 55 meV. This value is the largest ever reported in inverted (d_{QW} > 6.3 nm) HgTe QWs, is well above k_B T at room temperature, and is a necessary step towards room temperature QSH-based electronic devices. Furthermore, we have demonstrated that thick QWs can be transformed from semimetals to 2D TIs by changing their strain from tensile to compressive. Finally, we emphasize the accuracy of strain control via the SLS approach. The effective lattice constant of the SLS can be conveniently controlled by the product of CdTe-period growth time and Te beam-equivalent pressure, with both parameters straightforwardly accessible in crystal growth.

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*philipp.leubner@physik.uni-wuerzburg.de

[6] Alternatively, several μm thick buffer layers of fully relaxed CdTe on Si or GaAs can be employed.